EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	226127	(wafer or substrate or base or carrier or plate) near9 (holder or handler)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 08:34
L2	3428	(wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz$4 near9 (layer or film))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 08:36
L3	886	(wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz$4 near9 (layer or film)) and (heat$4 or thermal $4) near9 (device or circuit)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 08:36
L4	23	(wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz$4 near9 (layer or film)) and (heat$4 or thermal $4) near9 (device or circuit) and (oxidat $4 near gas)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 08:58
L5	23	(wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz$4 near9 (layer or film)) and (heat$4 or thermal $4) near9 (device or circuit) and (oxidat $4 near gas) and temperature	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 09:00

L6	10	(wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz$4 near9 (layer or film)) and (heat$4 or thermal $4) near9 (device or circuit) and (oxidat $4 near gas) and temperature and (process with temperature)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 09:04
L7	1	(wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz$4 near9 (layer or film)) and (heat$4 or thermal $4) near9 (device or circuit) and (oxidat $4 near gas) and temperature and (process with temperature) and (record with temperature)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 09:06
L8	1	(wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz$4 near9 (layer or film)) and (heat$4 or thermal $4) near9 (device or circuit) and (oxidat $4 near gas) and temperature and (process with temperature) and record	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 09:08

L9	10	(wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz$4 near9 (layer or film)) and (heat$4 or thermal $4) near9 (device or circuit) and (oxidat $4 near gas) and temperature and (process with temperature)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 09:08
L10	5	(wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz$4 near9 (layer or film)) and (heat$4 or thermal $4) near9 (device or circuit) and ((holder or handler) with graphite)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 10:19
L11	1	(wafer or substrate or base or carrier or plate) near9 (holder or handler) and (oxidiz$4 near9 (layer or film)) and (heat$4 or thermal $4) near9 (device or circuit) and ((holder or handler) with graphite) and (thermal near conductivity)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 10:21
L12	190	((holder or handler) with graphite) and (thermal near conductivity)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 10:21
L13	54	((holder or handler) with graphite) and (thermal near conductivity) with (holder or handler)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 10:22

L14	36	((holder or handler) with graphite) and (thermal near conductivity) with (holder or handler) and (temperature with (holder or handler))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 10:22
L15	32	((holder or handler) with graphite) and (thermal near conductivity) with (holder or handler) and (temperature with (holder or handler)) and (substrate or wafer or carrier or base or plate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/04/23 10:23
S1	369	(oxidiz$4 near9 (layer or film)) and (heat or anneal or thermal) near9 (substrate or wafer or carrier or base) and temperature and graphite and (GaAs or (gallium near arsenide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:05
S2	326	(oxidiz$4 near9 (layer or film)) and (heat or anneal or thermal) near9 (substrate or wafer or carrier or base) and temperature and graphite and (GaAs or (gallium near arsenide)) and (hold$4 or arm or support)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 11:22

S3	54	(oxidiz$4 near9 (layer or film)) and (heat or anneal or thermal) near9 device near9 (substrate or wafer or carrier or base) and temperature and graphite and (GaAs or (gallium near arsenide)) and (hold$4 or arm or support) and time	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 11:23
S4	7	(oxidiz$4 near9 (layer or film)) and (heat or anneal or thermal) near9 device near9 (substrate or wafer or carrier or base) and temperature and graphite and (GaAs or (gallium near arsenide)) and (hold$4 or arm or support) and time and condensat$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/18 11:24
S5	6712	(substrate or wafer or carrier or base) near9 (oxidiz$4 near (layer or film))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:06
S6	143	(substrate or wafer or carrier or base) near9 (oxidiz$4 near (layer or film)) and ((layer or film) near stack)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:07
S7	0	(substrate or wafer or carrier or base) near9 (oxidiz$4 near (layer or film)) and ((layer or film) near stack) and (heat$4 or thermal) and gas and temperature and thermistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:09

S8	0	(substrate or wafer or carrier or base) near9 (oxidiz$4 near (layer or film)) and ((layer or film) near stack) and (heat$4 or thermal) and gas and thermistor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:11
S9	14	(substrate or wafer or carrier or base) near9 (oxidiz$4 near (layer or film)) and ((layer or film) near stack) and (heat$4 or thermal) and gas and sensor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:11
S10	5	(substrate or wafer or carrier or base) near9 (oxidiz$4 near (layer or film)) and ((layer or film) near stack) and (heat$4 or thermal) and gas and ((heat or thermal) same sensor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:26
S11	1	(substrate or wafer or carrier or base) near9 (oxidiz$4 near (layer or film)) and ((layer or film) near stack) and (heat$4 or thermal) and gas and ((heat or thermal) same sensor) and graphite	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:28
S12	0	(substrate or wafer or carrier or base) near9 (oxidiz$4 near (layer or film)) and ((layer or film) near stack) and (heat$4 or thermal) and gas and ((heat or thermal) same sensor) and GaAs	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:34
S13	37	(substrate or wafer or carrier or base) near9 (oxidiz$4 near (layer or film)) and GaAs and graphite	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/09/26 11:35

| S14 | 3 | (substrate or wafer or carrier or base) near9 (oxidiz$4 near (layer or film)) and GaAs and graphite and thermocouple | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/09/26 11:41 |
| S15 | 3 | (substrate or wafer or carrier or base) near9 (oxidiz$4 near (layer or film)) and GaAs and graphite and thermocouple and laser | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2007/09/26 11:41 |

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